

Description

This 60V 300mA N-Channel MOSFET in a SOT-23 Plastic Package.

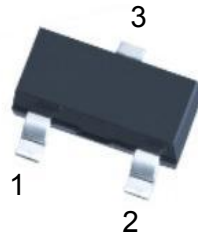
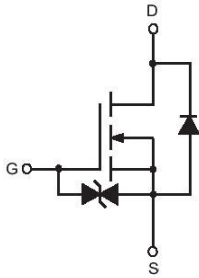
Applications

Intended for use in general purpose switching and phase control applications.

Features

- Sensitive gate trigger current and Low Holding current.
- ESD protected up to 2KV,
- Halogen-Free Product.

V_{DSS}	$R_{DS(on)}$ Typ	I_D
60V	1.7Ω	300mA

Equivalent Circuit & Pinning


PIN1 : Gate

PIN 2 : Source

PIN 3 : Drain

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Drain Current - Continuous	$I_D (Ta=25^\circ C)$	300	mA
	$I_D (Ta=85^\circ C)$	210	
Drain Current - Pulsed(Note 1)	I_{DM}	1200	mA
Gate-Source Voltage - Continuous	V_{GSS}	± 20	V
Power Dissipation	P_D	350	mW
Junction Temperature Range	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C
Maximum Junction-to-Ambient(Note 2)	$R_{\theta JA}(\text{Steady State})$	300	°C/W
	$R_{\theta JA}(t \leq 5s)$	92	

Note 1) Pulse Width 10us, Duty Cycle 1%

Note 2) Surface-mounted on FR4 board using 1 sq in pad size with 1 oz Cu

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS}=0$	$I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0$	$V_{DS}=60V$			1.0	μA
Gate-Source Leakage current	I_{GSS}	$V_{DS}=0V$	$V_{GS}=\pm 20V$			± 10	μA
Static Drain-Source On-Resistance	$R_{DS(on)(1)}$	$V_{GS}=10V$	$I_D=0.5A$			2.3	Ω
	$R_{DS(on)(2)}$	$V_{GS}=5V$	$I_D=0.05A$		1.7	2.7	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$	$I_S=250mA$			1.5	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu A$	1.0	1.6	2.5	V
Forward Transconductance	Y_{fs}	$V_{DS}=10V$	$I_D=0.2A$	80			mS
Input Capacitance	C_{iss}	$V_{GS}=0V, f=1MHz, V_{DS}=20V$			25	50	pF
Output Capacitance	C_{oss}				11	25	
Reverse Transfer Capacitance	C_{rss}				2.5	5	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=4.5V, V_{DS}=10V; I_D=200mA$			0.7		nC
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	Q_{GS}				0.3		
Gate-to-Drain Charge	Q_{GD}				0.1		

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(ON)}$	VGS =10V, VDD=25V, ID=500mA, RG=25Ω		6.0		ns
Rise Time	t_r			5.8		
Turn-Off Delay Time	$t_{d(OFF)}$			13.2		
Fall Time	t_f			8.9		

Electrical Characteristic Curve

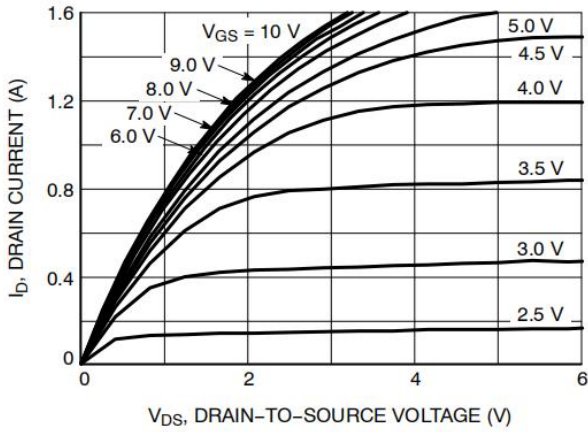


Figure 1. On-Region Characteristics

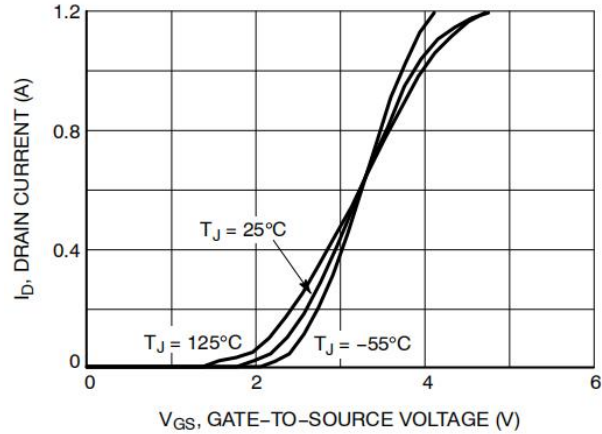


Figure 2. Transfer Characteristics

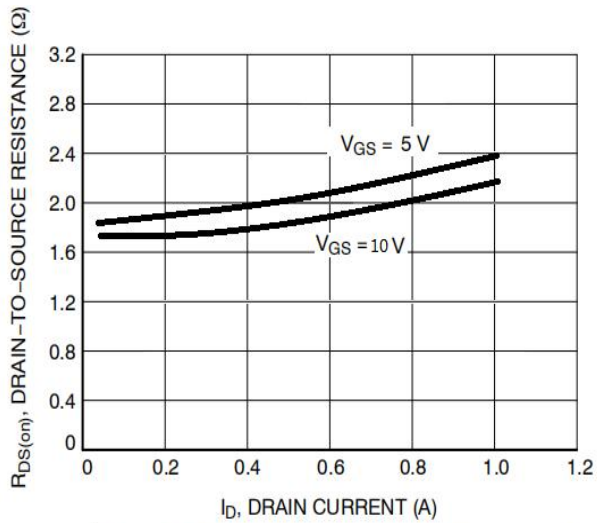


Figure 3. On-Resistance vs. Drain Current and Temperature

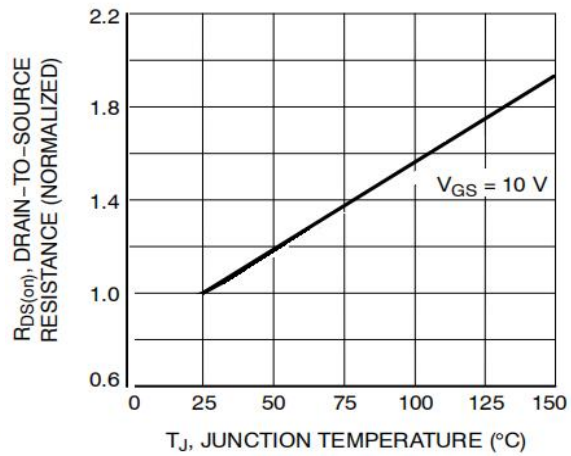


Figure 4 On-Resistance Variation with Temperature

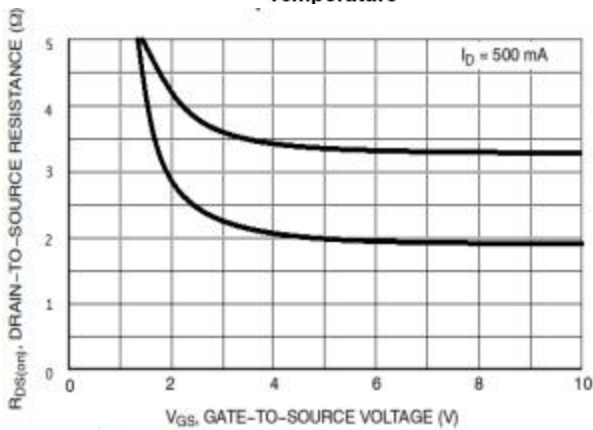


Figure 5. On-Resistance vs. Gate-to-Source Voltage

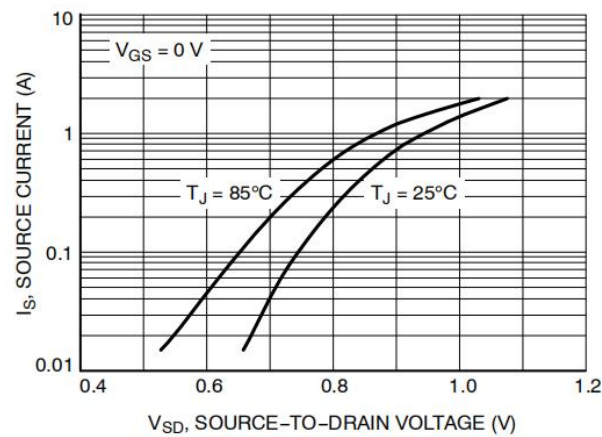


Figure 6 Diode Forward Voltage vs. Current

Electrical Characteristic Curve

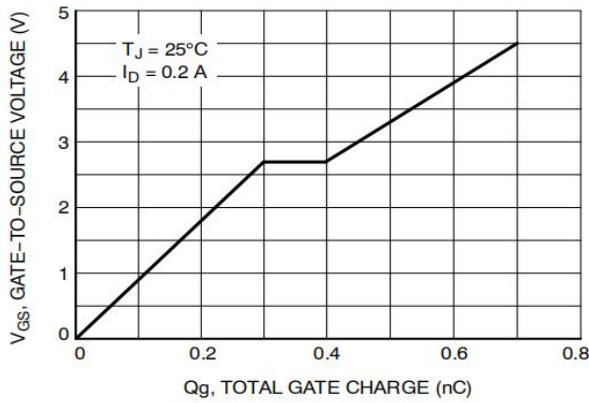


Figure 7 . Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

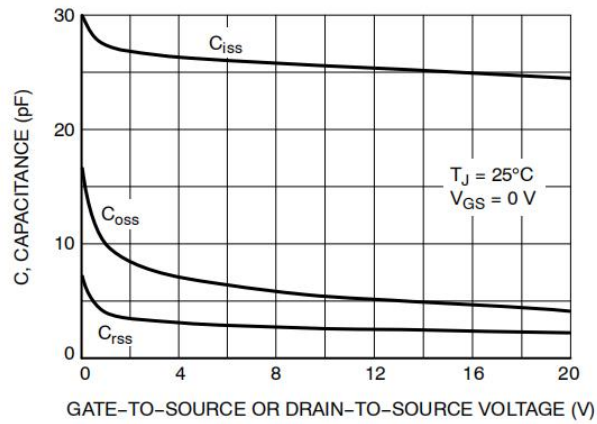


Figure 8 . Capacitance Variation

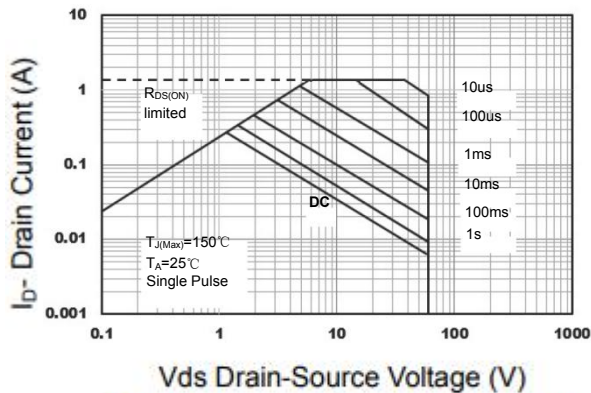


Figure 9 : Safe Operation Area

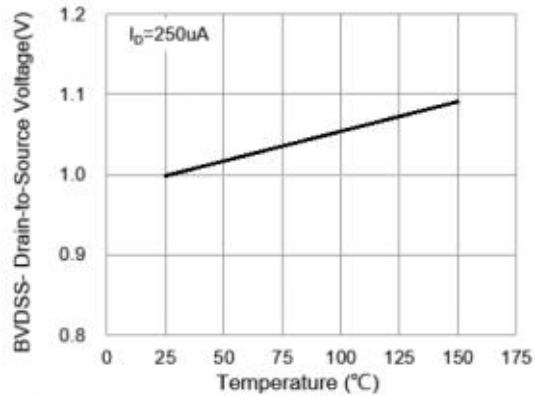


Figure 10 : Breakdown Voltage vs. Temperature

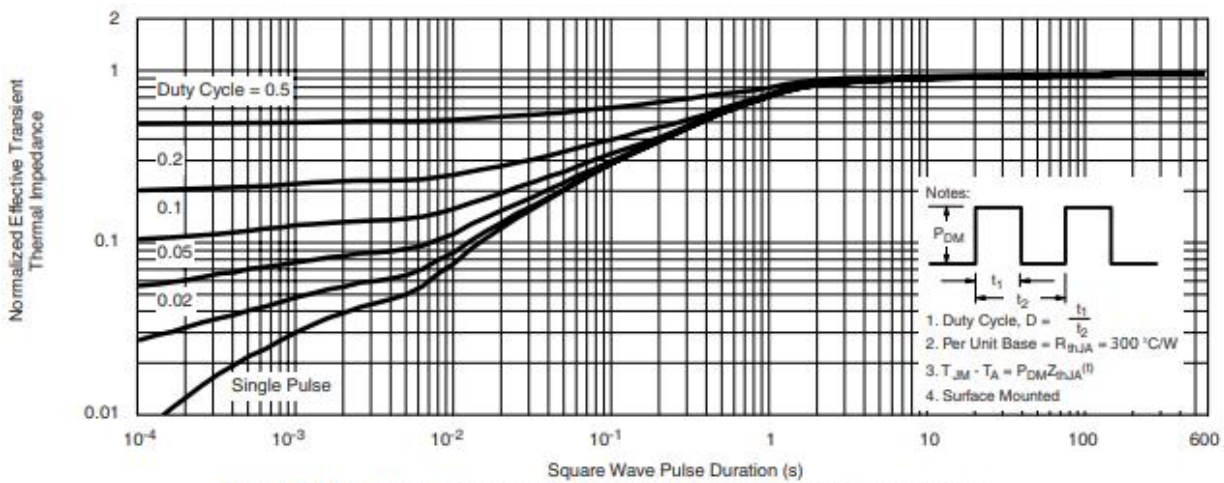
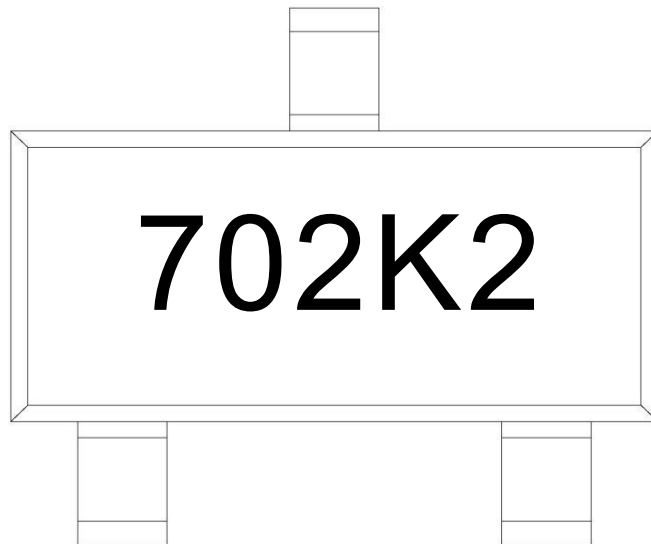


Figure 11 : Normalized Thermal Transient Impedance, Junction-to-Ambient

Marking Instructions



Note:

702K2: Product Type

Packaging SPEC.

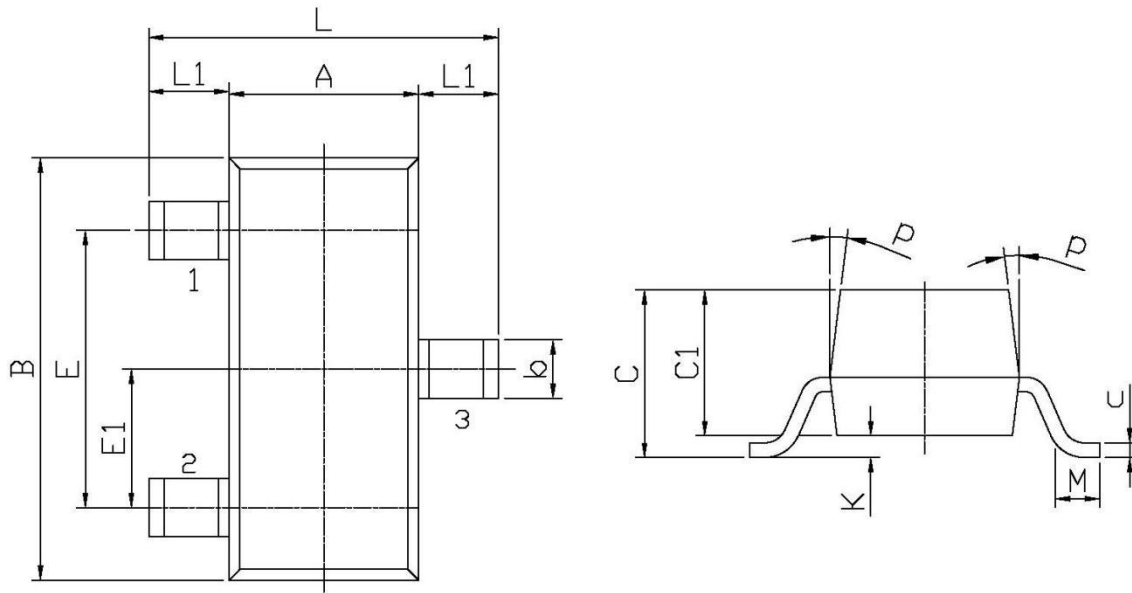
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7" x8	180x120x180	390x385x205

Package Outline Dimensions

SOT-23

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			